

IN THE CLAIMS:

1-10. (Canceled)

11. (Currently Amended) A process of manufacturing a semiconductor device, comprising:

forming a first insulating film above a semiconductor substrate;

removing a selected portion of the first insulating film, thereby forming an opening;

depositing a first electrode, a dielectric film and a second electrode successively on a bottom portion of the opening in substantially parallel relationship with a surface of the semiconductor substrate;

removing selected portions of the first electrode, the dielectric film and the second electrode, and forming a capacitor at a selected position in the opening;

forming a second insulating film at least in the opening; and

forming a third insulating film on the second insulating film.

12. (Original) The process of manufacturing a semiconductor device according to claim 11, further comprising forming a diffusion preventing film on which the first insulating film is formed.

13. (Original) The process of manufacturing a semiconductor device according to claim 11, further comprising forming a diffusion preventing film between the capacitor and the second insulating film.

14. (Original) The process of manufacturing a semiconductor device according to claim 11, further comprising: forming a first diffusion preventing film on which the first insulating film is formed; and forming a second diffusion preventing film between the capacitor and the second insulating film.

15. (Original) The process of manufacturing a semiconductor device according to claim 11, wherein the first insulating film is one of a low dielectric film, a diffusion preventing film and a laminated film formed of the low dielectric film and the diffusion preventing film.

16. (Original) The process of manufacturing a semiconductor device according to claim 11, wherein the third insulating film is a low dielectric film, and the second insulating film comprises a relative dielectric constant higher than the third insulating film.

17. (Original) The process of manufacturing a semiconductor device according to claim 11, wherein the second insulating film is a coated organic insulating film.

18. (Original) The process of manufacturing a semiconductor device according to claim 11, wherein the capacitor is thinner than the first insulating film.

19. (Original) The process of manufacturing a semiconductor device according to claim 11, wherein the second insulating film is formed only in the opening.

20. (Original) The process of manufacturing a semiconductor, device according to claim 11, further comprising:

forming the second insulating film on the first insulating film and the capacitor;

and

flattening the second insulating film by CMP until a surface of the first insulating film is exposed.

21. (New) The process of manufacturing a semiconductor device according to claim 11, further comprising:

forming a fourth insulating film being a low dielectric film below the first insulating film; and

forming a wire in the fourth insulating film.

22. (New) The process of manufacturing a semiconductor device according to claim 11,

wherein the third insulating film is formed on the first and the second insulating film and is a low dielectric film,

the process further comprising:

forming a connecting member in the first and the third insulating films; and

forming a wire in the third insulating film.

23. (New) The process of manufacturing a semiconductor device according to claim 11,
wherein the capacitor is formed apart from the first insulating film.